

BUK661R6-30C

N-channel TrenchMOS intermediate level FET

Rev. 01 — 6 September 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for intermediate level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$		-	-	30	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u>	<u>1]</u>	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 16}}{\text{ or } 16}$		-	1.4	1.6	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 100 \text{ A}; V_{sup} \le 30 \text{ V};$ $R_{GS} = 50 \Omega; V_{GS} = 10 \text{ V};$ $T_{j(init)} = 25 ^{\circ}C; unclamped$	-	-	1.707	J
Dynamic cl	Dynamic characteristics					
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 24 V; V_{GS} = 10 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	63	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK661R6-30C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

_	A !!!!				
Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
	DC	[2]	-16	16	V
drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V; \text{see } \underline{\text{Figure 1}}$	[3]	-	120	Α
	T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1	[3]	-	120	Α
peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3		-	1310	Α
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
storage temperature			-55	175	°C
junction temperature			-55	175	°C
diode					
source current	T _{mb} = 25 °C	[3]	-	120	Α
peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	1310	Α
ggedness					
non-repetitive drain-source avalanche energy	I_D = 100 A; $V_{sup} \le$ 30 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	1.707	J
repetitive drain-source avalanche energy		[4][5][6]	-	-	J
	gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature diode source current peak source current ggedness non-repetitive drain-source avalanche energy repetitive drain-source	$ \begin{array}{lll} drain\text{-source voltage} & T_j \geq 25 \ ^\circ\text{C}; T_j \leq 175 \ ^\circ\text{C} \\ \\ gate\text{-source voltage} & Pulsed \\ \hline DC \\ \\ drain current & T_{mb} = 25 \ ^\circ\text{C}; V_{GS} = 10 \ \text{V}; see \ \underline{Figure} \ 1 \\ \hline T_{mb} = 100 \ ^\circ\text{C}; V_{GS} = 10 \ \text{V}; see \ \underline{Figure} \ 1 \\ \hline peak drain current & T_{mb} = 25 \ ^\circ\text{C}; t_p \leq 10 \ \mu\text{s}; pulsed; see \ \underline{Figure} \ 3 \\ \hline total power dissipation & T_{mb} = 25 \ ^\circ\text{C}; see \ \underline{Figure} \ 2 \\ \hline storage temperature \\ \hline junction temperature \\ \hline diode & \\ \hline source current & T_{mb} = 25 \ ^\circ\text{C} \\ \hline peak source current & T_{p} \leq 10 \ \mu\text{s}; pulsed; T_{mb} = 25 \ ^\circ\text{C} \\ \hline gedness & \\ \hline non-repetitive drain-source \\ avalanche energy & V_{GS} = 10 \ \text{V}; T_{j(init)} = 25 \ ^\circ\text{C}; unclamped \\ \hline repetitive drain-source & \\ \hline \end{array} $	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$

^[1] Accumulated pulse duration not to exceed 5mins.

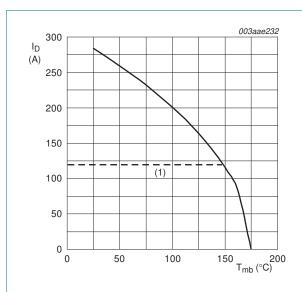
^{[2] -16}V accumulated duration not to exceed 168 hrs.

^[3] Continuous current is limited by package.

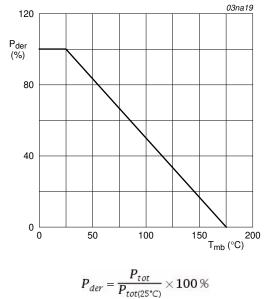
^[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}$ C.

^[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[6] Refer to application note AN10273 for further information.

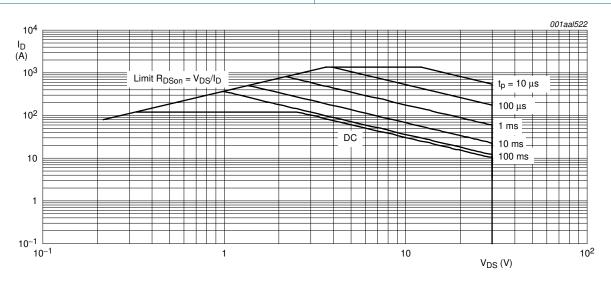


 $V_{\rm GS} \geq$ 10 V(1) Capped at 120 A due to package.



Continuous drain current as a function of Fig 1. mounting base temperature

Normalized total power dissipation as a Fig 2. function of mounting base temperature



 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse (1) Capped at 100 A due to package.

Safe operating area; continuous and peak drain currents as a function of drain-source voltage Fig 3.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

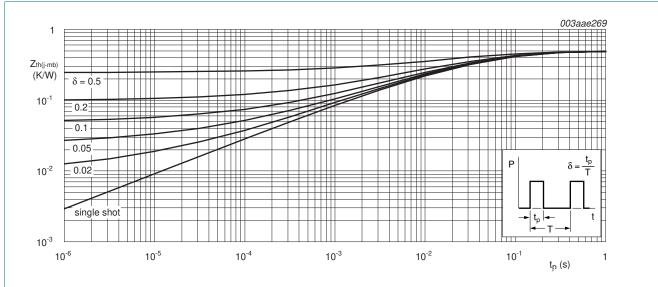


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	٧
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 9; see Figure 10	1.8	2.3	2.8	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	3.3	V
		$I_D = 2.5 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 10	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I _{GSS} gate leakage current		$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 16	-	1.4	1.6	mΩ
	$\overline{V_G}$	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 16	-	2.1	3.3	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 16	-	1.7	2.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 11	-	-	3.2	mΩ
Dynamic	characteristics					
Q _{G(tot)} total gate charge		$I_D = 25 \text{ A}$; $V_{DS} = 24 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 12; see Figure 13	-	229	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 24 \text{ V}$; $V_{GS} = 5 \text{ V}$; see Figure 12; see Figure 13	-	131	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	38	-	nC
Q_{GD}	gate-drain charge	see Figure 12; see Figure 13	-	63	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	11223	14964	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	1780	2136	pF
C _{rss}	reverse transfer capacitance		-	1085	1486	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 1 \Omega; V_{GS} = 10 \text{ V};$	-	53	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	114	-	ns
t _{d(off)}	turn-off delay time		-	363	-	ns
t _f	fall time		-	192	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L _S	internal source inductance	from source lead to source bond pad ; $T_j = 25 ^{\circ} C$	-	7.5	-	nΗ

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 15</u>	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	70	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}$	-	0.138	-	nC

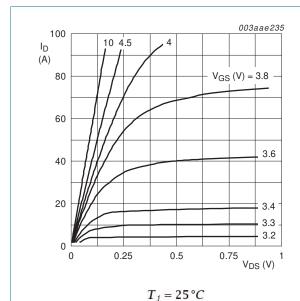


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

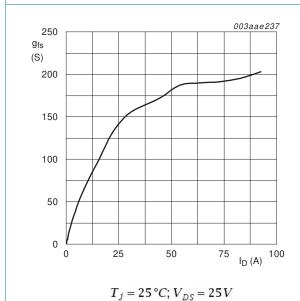


Fig 7. Forward transconductance as a function of drain current; typical values

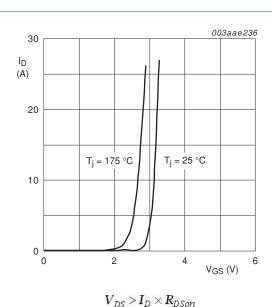


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

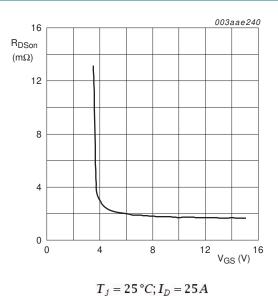


Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

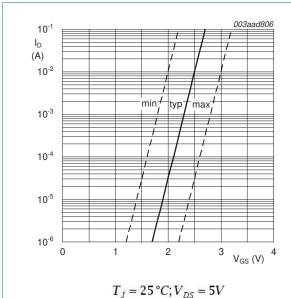


Fig 9. Sub-threshold drain current as a function of gate-source voltage

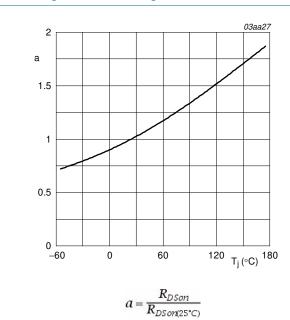
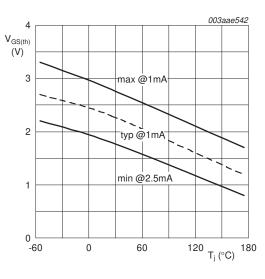


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature



 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature

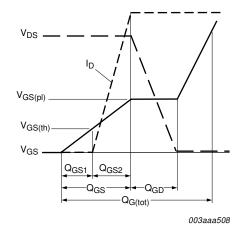


Fig 12. Gate charge waveform definitions

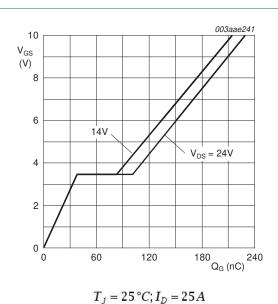
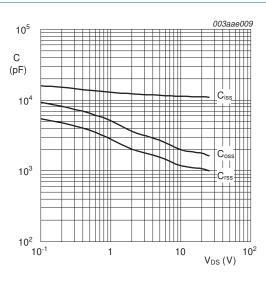


Fig 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V; f = 1 MHz$

Fig 14. Input, output and reverse transfer capacitance as a function of drain-source voltage; typical values

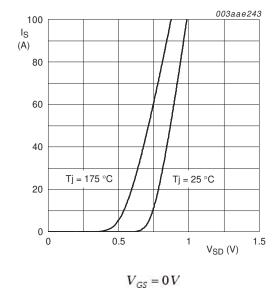
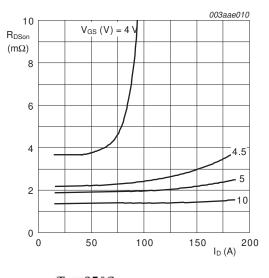


Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values



 $T_j = 25\,^{\circ}C$

Fig 16. Drain-source on-state resistance as a function of drain current; typical values

7. Package outline

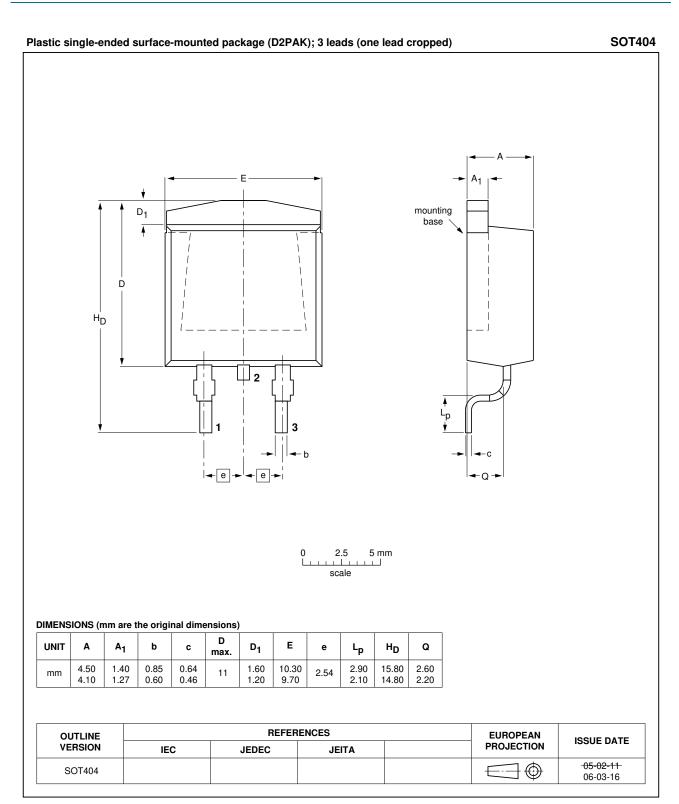


Fig 17. Package outline SOT404 (D2PAK)

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N-channel TrenchMOS intermediate level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK661R6-30C v.1	20100906	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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